

STGW25H120F2 Datasheet



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DiGi Electronics Part Number	STGW25H120F2-DG
Manufacturer	STMicroelectronics
Manufacturer Product Number	STGW25H120F2
Description	IGBT H-SERIES 1200V 25A TO-247
Detailed Description	IGBT Trench Field Stop 1200 V 50 A 375 W Through Hole TO-247-3

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Manufacturer Product Number:

STGW25H120F2

Series:

-

IGBT Type:

Trench Field Stop

Current - Collector (Ic) (Max):

50 A

Vce(on) (Max) @ Vge, Ic:

2.6V @ 15V, 25A

Switching Energy:

600µJ (on), 700µJ (off)

Gate Charge:

100 nC

Test Condition:

600V, 25A, 100hm, 15V

Mounting Type:

Through Hole

Supplier Device Package:

TO-247-3

Manufacturer:

STMicroelectronics

Product Status:

Active

Voltage - Collector Emitter Breakdown (Max):

1200 V

Current - Collector Pulsed (Icm):

100 A

Power - Max:

375 W

Input Type:

Standard

Td (on/off) @ 25°C:

29ns/130ns

Operating Temperature:

-55°C ~ 175°C (TJ)

Package / Case:

TO-247-3

Base Product Number:

STGW25

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

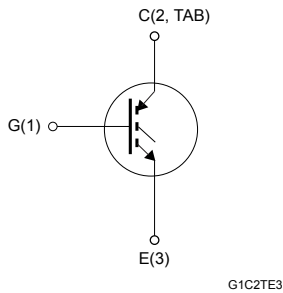
EAR99



STGW25H120F2, STGWA25H120F2

Datasheet

Trench gate field-stop IGBT, H series 1200 V, 25 A high speed



Features

- Maximum junction temperature: $T_J = 175\text{ °C}$
- High speed switching series
- Minimized tail current
- $V_{CE(sat)} = 2.1\text{ V (typ.) @ } I_C = 25\text{ A}$
- $5\text{ }\mu\text{s}$ minimum short circuit withstand time at $T_J = 150\text{ °C}$
- Safe paralleling
- Low thermal resistance

Applications

- Photovoltaic inverters
- Uninterruptible power supply
- Welding
- Power factor correction
- High frequency converters



Product status links

[STGW25H120F2](#)

[STGWA25H120F2](#)

Product summary

Order code	STGW25H120F2
Marking	G25H120F2
Package	TO-247
Packing	Tube
Order code	STGWA25H120F2
Marking	G25H120F2
Package	TO-247 long leads
Packing	Tube

Description

These devices are IGBTs developed using an advanced proprietary trench gate field-stop structure. The device is part of the H series IGBTs, which represent an optimum compromise between conduction and switching losses to maximize the efficiency of high-switching frequency converters. Furthermore, a slightly positive $V_{CE(sat)}$ temperature coefficient and very tight parameter distribution result in safer paralleling operation.



1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GE} = 0\text{ V}$)	1200	V
I_C	Continuous collector current at $T_C = 25\text{ °C}$	50	A
	Continuous collector current at $T_C = 100\text{ °C}$	25	
$I_{CP}^{(1)}$	Pulsed collector current	100	A
V_{GE}	Gate-emitter voltage	± 20	V
P_{TOT}	Total power dissipation at $T_C = 25\text{ °C}$	375	W
T_J	Operating junction temperature range	- 55 to 175	$^{\circ}\text{C}$
T_{STG}	Storage temperature range	- 55 to 150	$^{\circ}\text{C}$

1. Pulse width limited by maximum junction temperature.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.4	$^{\circ}\text{C/W}$
R_{thJA}	Thermal resistance, junction-to-ambient	50	$^{\circ}\text{C/W}$



2 Electrical characteristics

$T_J = 25\text{ °C}$ unless otherwise specified.

Table 3. Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$, $I_C = 2\text{ mA}$	1200			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 25\text{ A}$		2.1	2.6	V
		$V_{GE} = 15\text{ V}$, $I_C = 25\text{ A}$, $T_J = 125\text{ °C}$		2.4		
		$V_{GE} = 15\text{ V}$, $I_C = 25\text{ A}$, $T_J = 175\text{ °C}$		2.5		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 1\text{ mA}$	5	6	7	V
I_{CES}	Collector cut-off current	$V_{GE} = 0\text{ V}$, $V_{CE} = 1200\text{ V}$			25	μA
I_{GES}	Gate-emitter leakage current	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			± 250	nA

Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0\text{ V}$	-	2010	-	pF
C_{oes}	Output capacitance		-	146	-	pF
C_{res}	Reverse transfer capacitance		-	49	-	pF
Q_g	Total gate charge	$V_{CC} = 960\text{ V}$, $I_C = 25\text{ A}$, $V_{GE} = 0\text{ to }15\text{ V}$ (see Figure 22)	-	100	-	nC
Q_{ge}	Gate-emitter charge		-	11	-	nC
Q_{gc}	Gate-collector charge		-	52	-	nC



Table 5. Switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 600\text{ V}$, $I_C = 25\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$ (see Figure 21)		29	-	ns
t_r	Current rise time			12	-	ns
$(di/dt)_{on}$	Turn-on current slope			1774	-	A/ μ s
$t_{d(off)}$	Turn-off delay time			130	-	ns
t_f	Current fall time			106	-	ns
$E_{on}^{(1)}$	Turn-on switching energy			0.6	-	mJ
$E_{off}^{(2)}$	Turn-off switching energy			0.7	-	mJ
E_{ts}	Total switching energy			1.3	-	mJ
$t_{d(on)}$	Turn-on delay time		$V_{CE} = 600\text{ V}$, $I_C = 25\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$ (see Figure 21)		27.5	-
t_r	Current rise time			13.5	-	ns
$(di/dt)_{on}$	Turn-on current slope			1522	-	A/ μ s
$t_{d(off)}$	Turn-off delay time			139	-	ns
t_f	Current fall time			200	-	ns
$E_{on}^{(1)}$	Turn-on switching energy			1.05	-	mJ
$E_{off}^{(2)}$	Turn-off switching energy			1.65	-	mJ
E_{ts}	Total switching energy			2.7	-	mJ
t_{sc}	Short-circuit withstand time	$V_{CE} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$,		5		-

1. Including the reverse recovery of the diode.
2. Including the tail of the collector current.



2.1 Electrical characteristics (curves)

Figure 1. Power dissipation vs case temperature

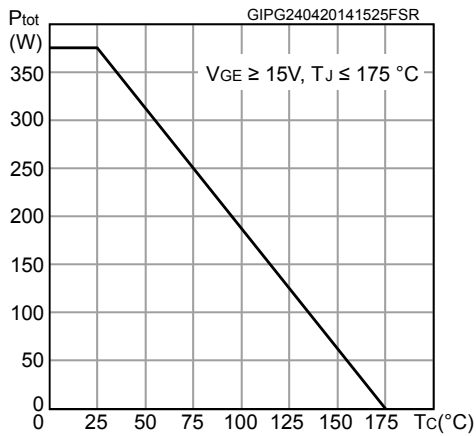


Figure 2. Collector current vs case temperature

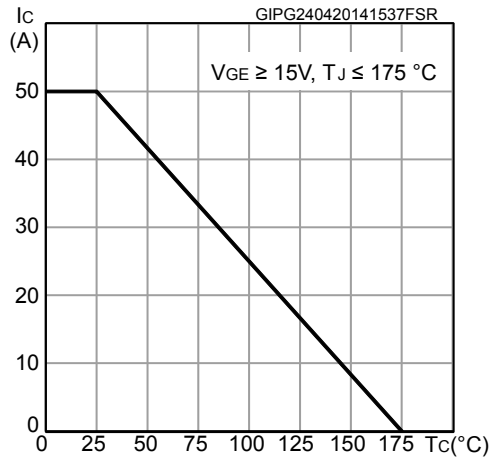


Figure 3. Output characteristics (T_J = 25 °C)

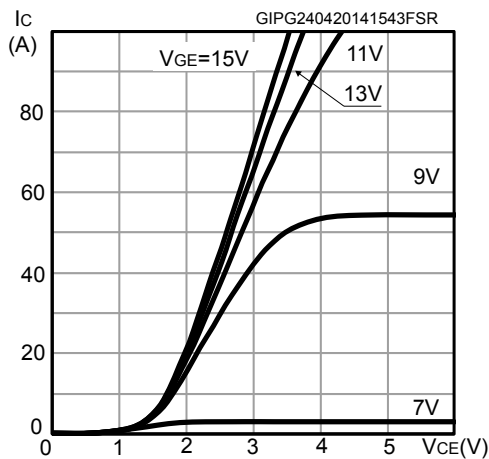


Figure 4. Output characteristics (T_J = 175 °C)

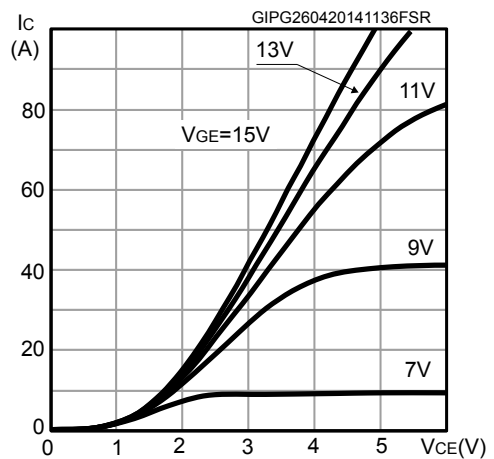


Figure 5. V_{CE(sat)} vs junction temperature

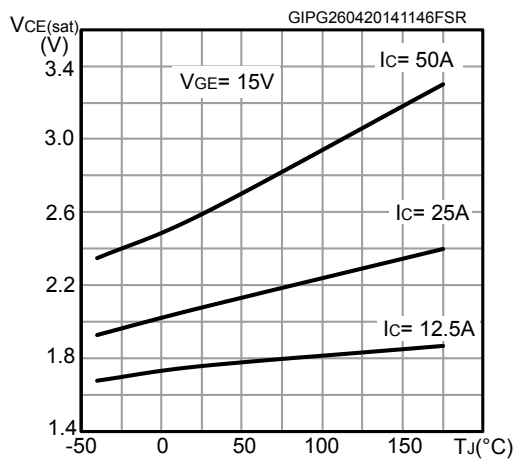


Figure 6. V_{CE(sat)} vs collector current

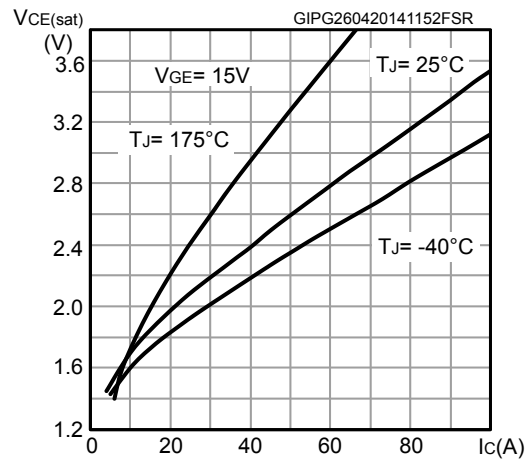




Figure 7. Collector current vs switching frequency

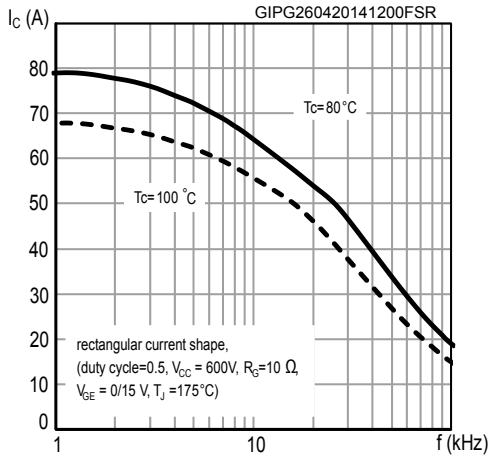


Figure 8. Safe operating area

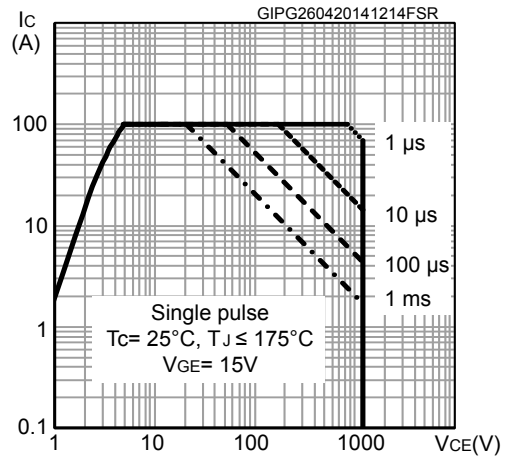


Figure 9. Transfer characteristics

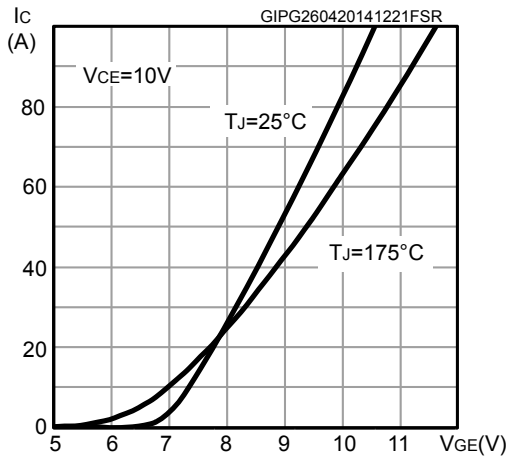


Figure 10. Diode V_F vs forward current

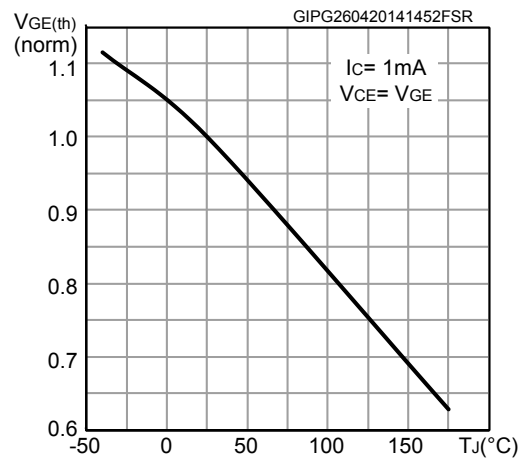


Figure 11. Normalized V_{(BR)CES} vs junction temperature

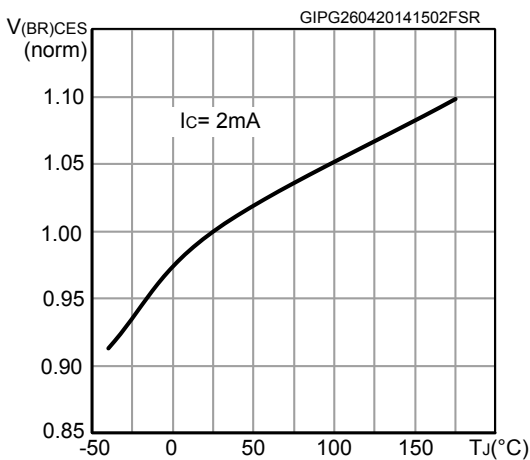


Figure 12. Capacitance variations

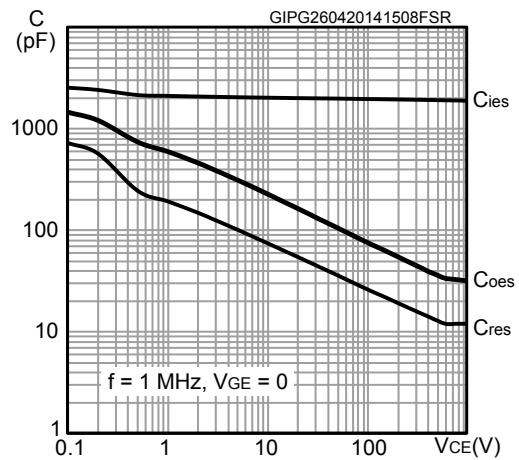




Figure 13. Gate charge vs gate-emitter voltage

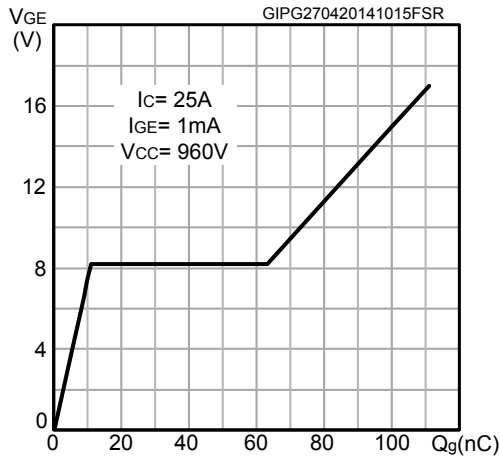


Figure 14. Switching energy vs collector current

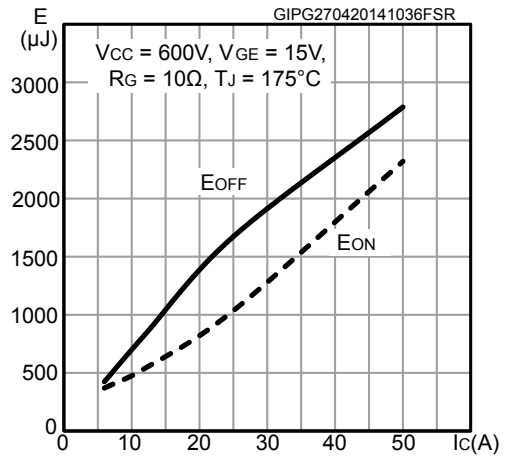


Figure 15. Switching energy vs gate resistance

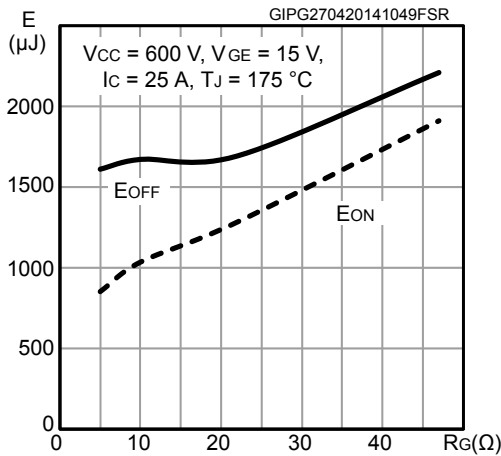


Figure 16. Switching energy vs junction temperature

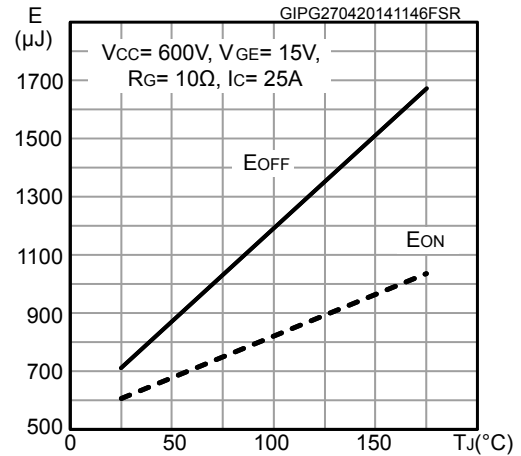


Figure 17. Switching energy vs collector-emitter voltage

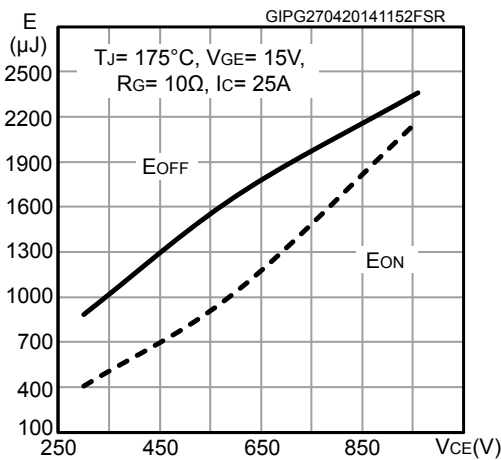


Figure 18. Switching times vs collector current

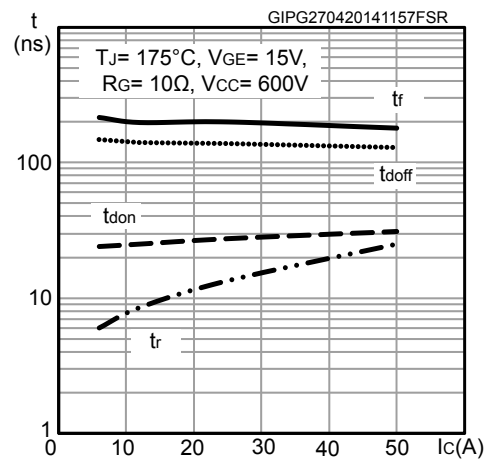




Figure 19. Switching times vs gate resistance

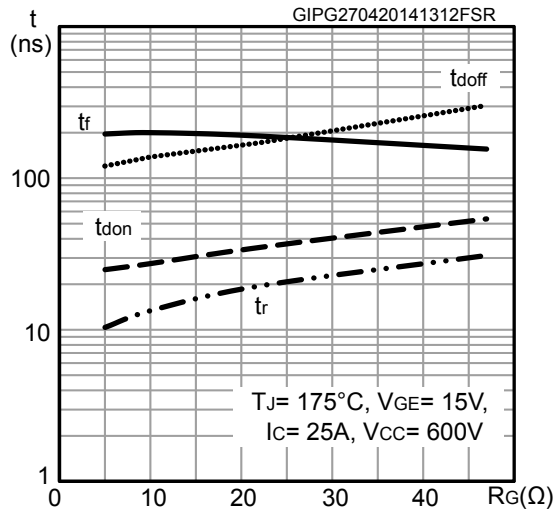
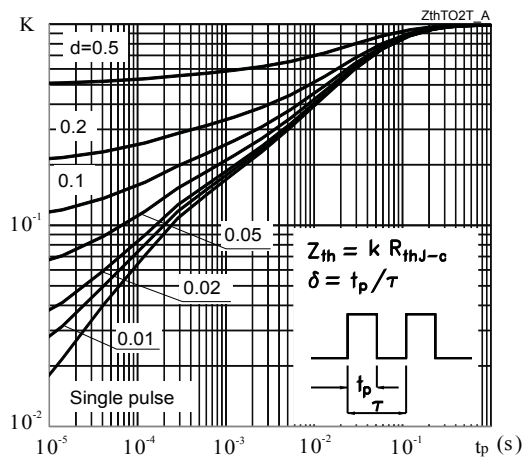


Figure 20. Thermal impedance





3 Test circuits

Figure 21. Test circuit for inductive load switching

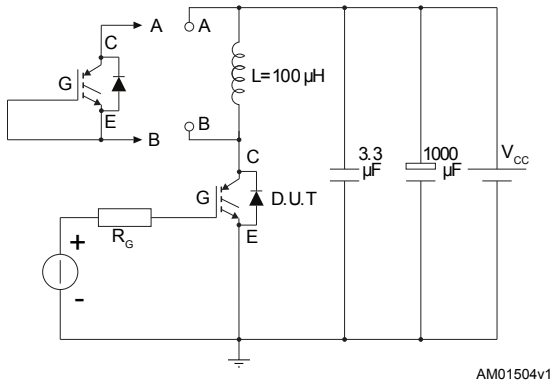


Figure 22. Gate charge test circuit

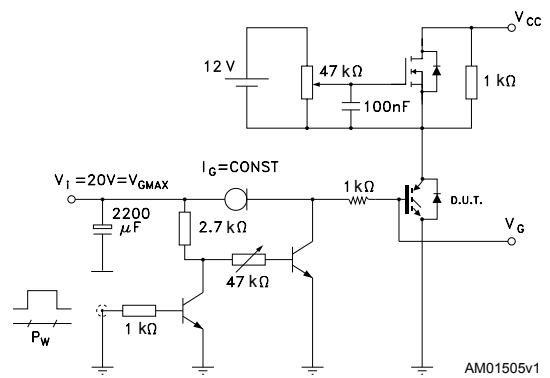
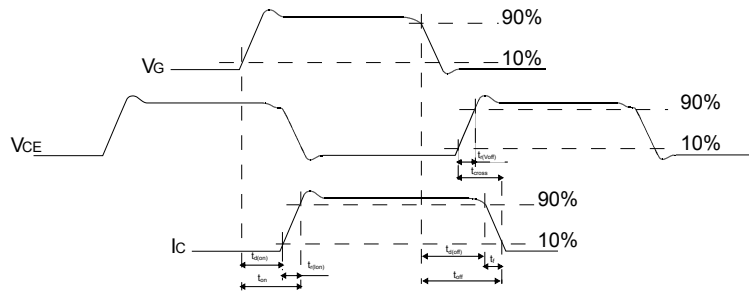


Figure 23. Switching waveform



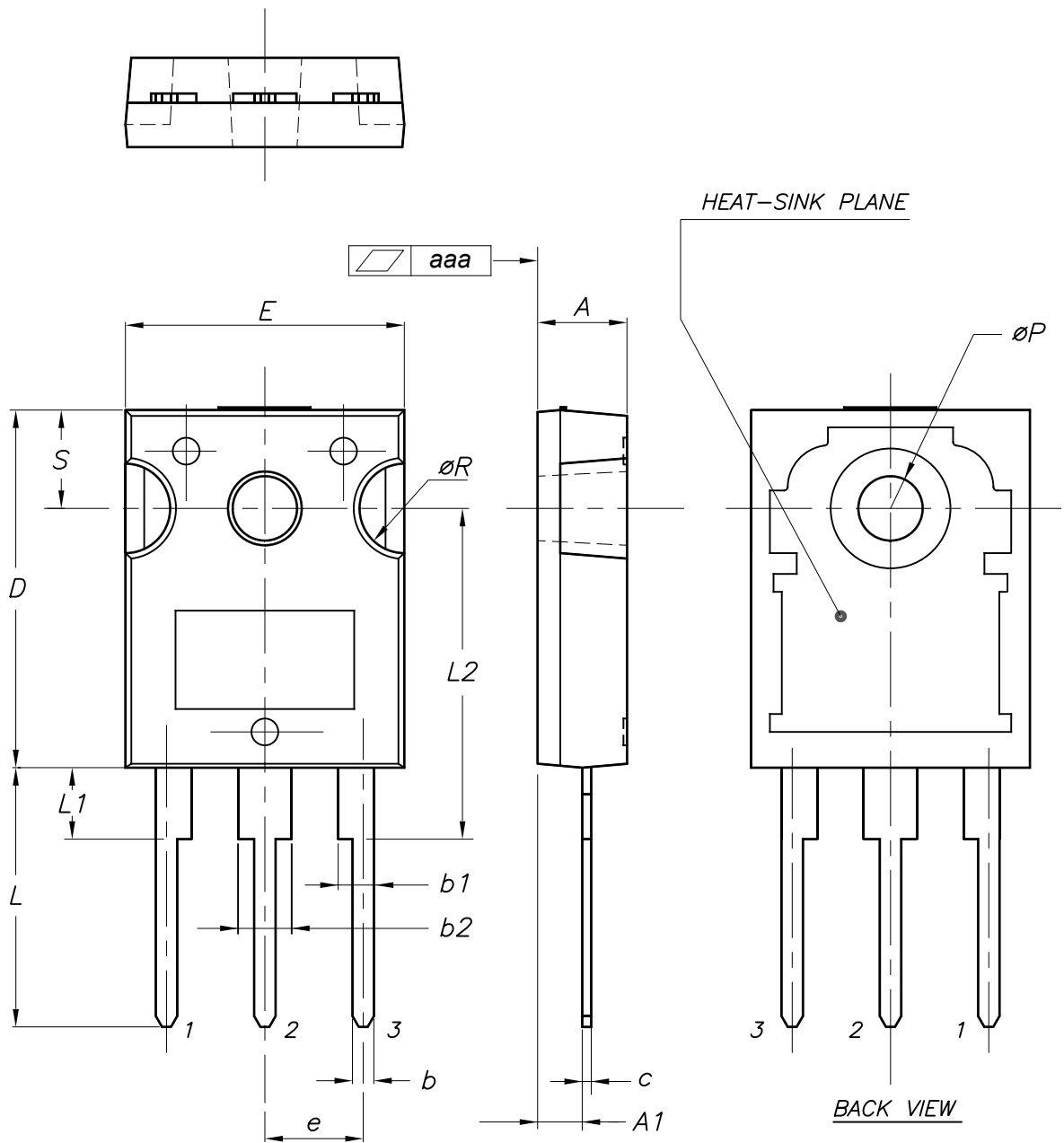
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4 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-247 package information

Figure 24. TO-247 package outline



0075325_10



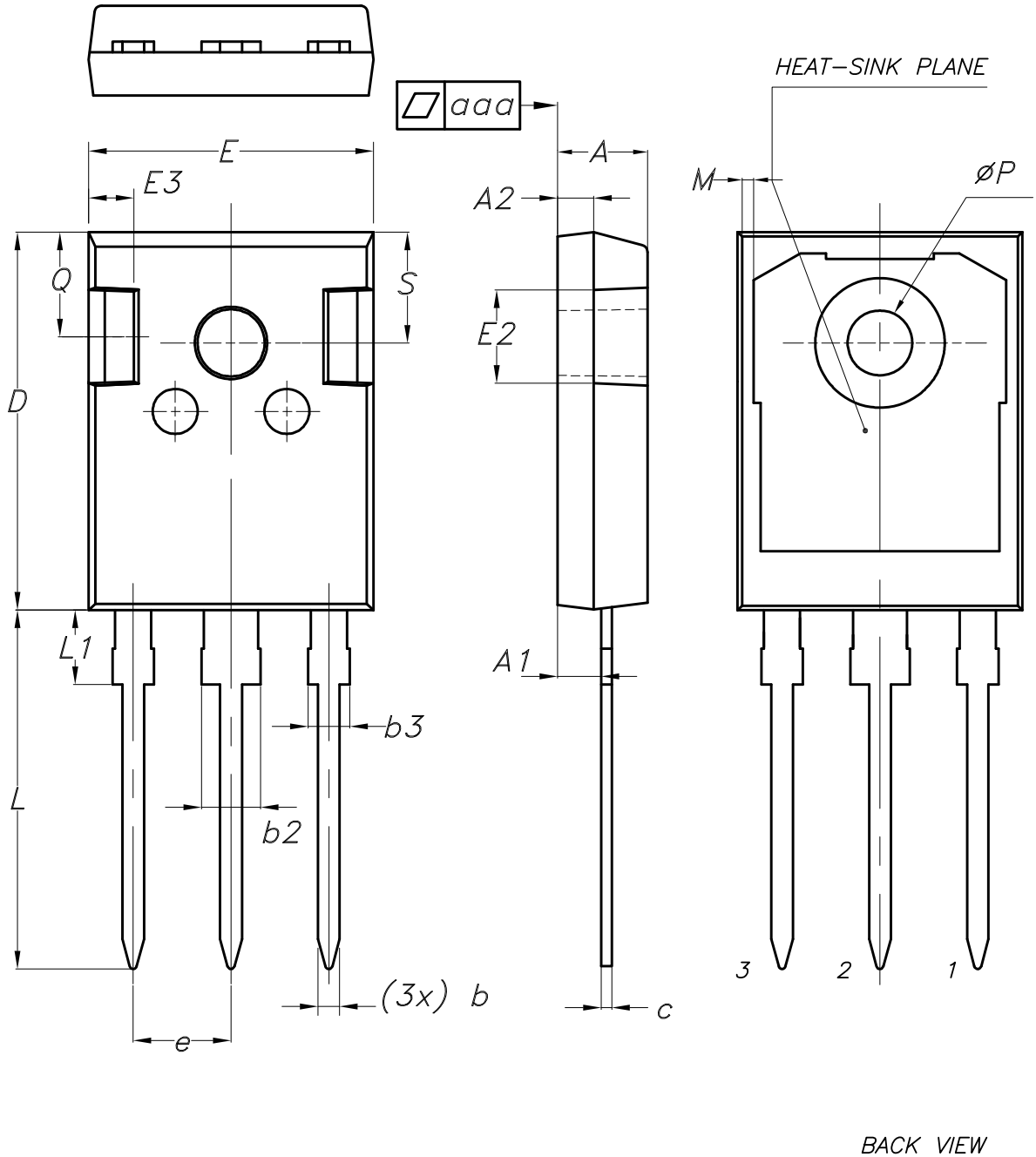
Table 6. TO-247 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70
aaa		0.04	0.10



4.2 TO-247 long leads package information

Figure 25. TO-247 long leads package outline



BACK VIEW

8463846_5



Table 7. TO-247 long leads package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.26
b2			3.25
b3			2.25
c	0.59		0.66
D	20.90	21.00	21.10
E	15.70	15.80	15.90
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	5.34	5.44	5.54
L	19.80	19.92	20.10
L1			4.30
M	0.35		0.95
P	3.50	3.60	3.70
Q	5.60		6.00
S	6.05	6.15	6.25
aaa		0.04	0.10



Revision history

Table 8. Document revision history

Date	Revision	Changes
28-Feb-2014	1	Initial release.
31-Mar-2014	2	Document status changed from preliminary to production data. Updated <i>Table 4: Static characteristics</i> and <i>Table 6: Switching characteristics (inductive load)</i> . Added Section 2.1: <i>Electrical characteristics (curves)</i> .
06-Mar-2015	3	Added 4.2: <i>TO-247 long leads, package information</i> . Updated Features and <i>Figure 23.: Gate charge test circuit</i> . Minor text changes
23-Mar-2015	4	Removed figures with diode. Minor text changes.
11-Feb-2025	5	Updated Section 4.1: TO-247 package information , and Section 4.2: TO-247 long leads package information . Minor text changes.



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